

General Description

The CMSA013N04L uses advanced SGT technology to provide excellent RDS(ON). This is suitable device for Synchronous Rectification for Server and general purpose applications.

Features

- Low On-Resistance
- 100% avalanche tested
- Small Footprint (5x6 mm) for Compact Design
- RoHS Compliant

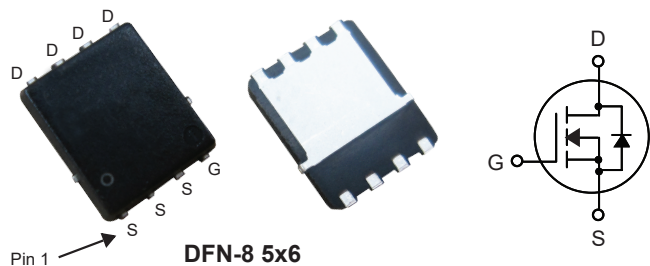
Product Summary

BVDSS	R _{DS(on)} max.	ID
40V	1.4mΩ	260A

Applications

- DC-DC Converters

DFN-8 5x6 Pin Configuration



Type	Package	Marking
CMSA013N04L	DFN-8 5x6	CMSA013N04L

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current	260	A
I _D @T _C =100°C	Continuous Drain Current	180	A
I _{DM}	Pulsed Drain Current	1040	A
EAS	Single Pulse Avalanche Energy ¹	1104	mJ
P _D @T _C =25°C	Total Power Dissipation	160	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient(min. footprint)	---	62	°C/W
R _{θJC}	Thermal Resistance Junction-case	---	0.78	°C/W

Electrical Characteristics($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=20A$	---	1.2	1.4	mΩ
		$V_{GS}=4.5V$, $I_D=20A$	---	1.6	2	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.0	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=40V$, $V_{GS}=0V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=20A$	---	57	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1.2	---	Ω
Q_g	Total Gate Charge	$I_D=50A$	---	92.6	---	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=20V$	---	23.5	---	
Q_{gd}	Gate-Drain Charge	$V_{GS}=10V$	---	12.3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=20V$ $V_{GS}=10V$ $R_{G(ext)}=1.6\Omega$	---	26.4	---	ns
T_r	Rise Time		---	8.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	76	---	
T_f	Fall Time		---	8.6	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	5200	---	pF
C_{oss}	Output Capacitance		---	1500	---	
C_{rss}	Reverse Transfer Capacitance		---	100	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	260	A
I_{SM}	Pulsed Source Current		---	---	1040	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=20A$, $T_J=25^{\circ}\text{C}$	---	0.74	1.2	V
t_{rr}	Reverse Recovery Time	$di/dt=100A/\mu s$	---	56	---	ns
Q_{rr}	Reverse Recovery Charge	$I_F=20A$	---	65.5	---	nC

Note :

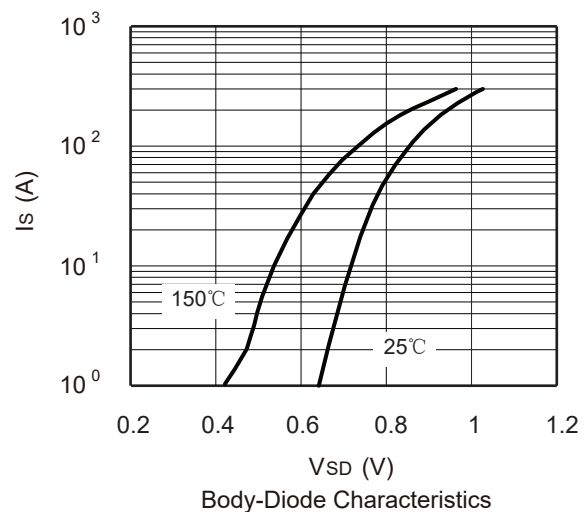
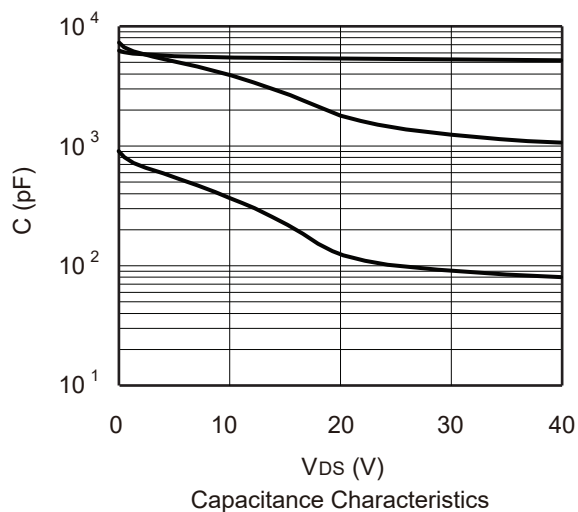
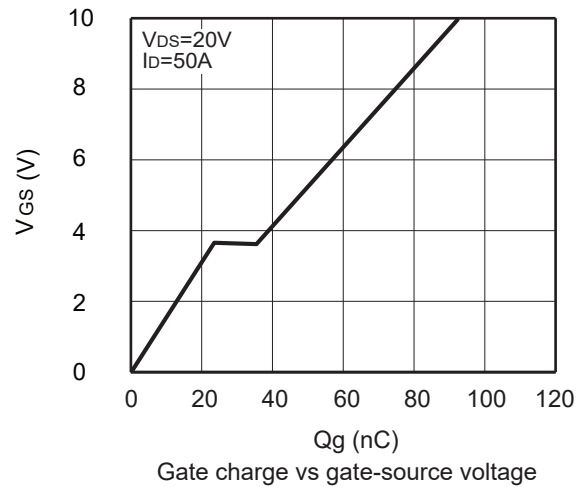
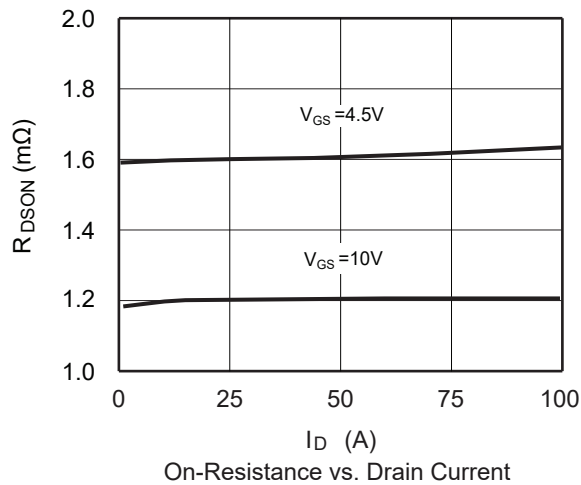
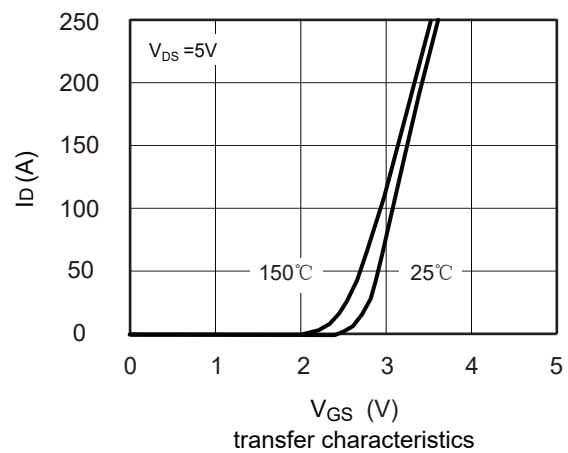
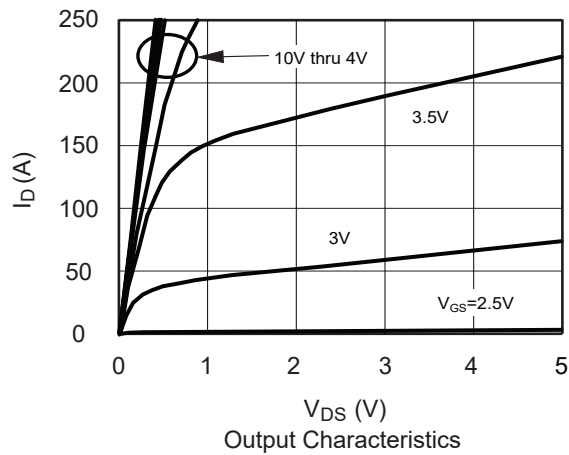
1.The EAS data shows Max. rating . The test condition is $V_{DD}=30V$, $V_{GS}=10V$, $L=1\text{mH}$, $I_{AS}=47A$.

This product has been designed and qualified for the consumer market.

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Cmos reserves the right to improve product design, functions and reliability without notice. Please refer to the latest version of specification.

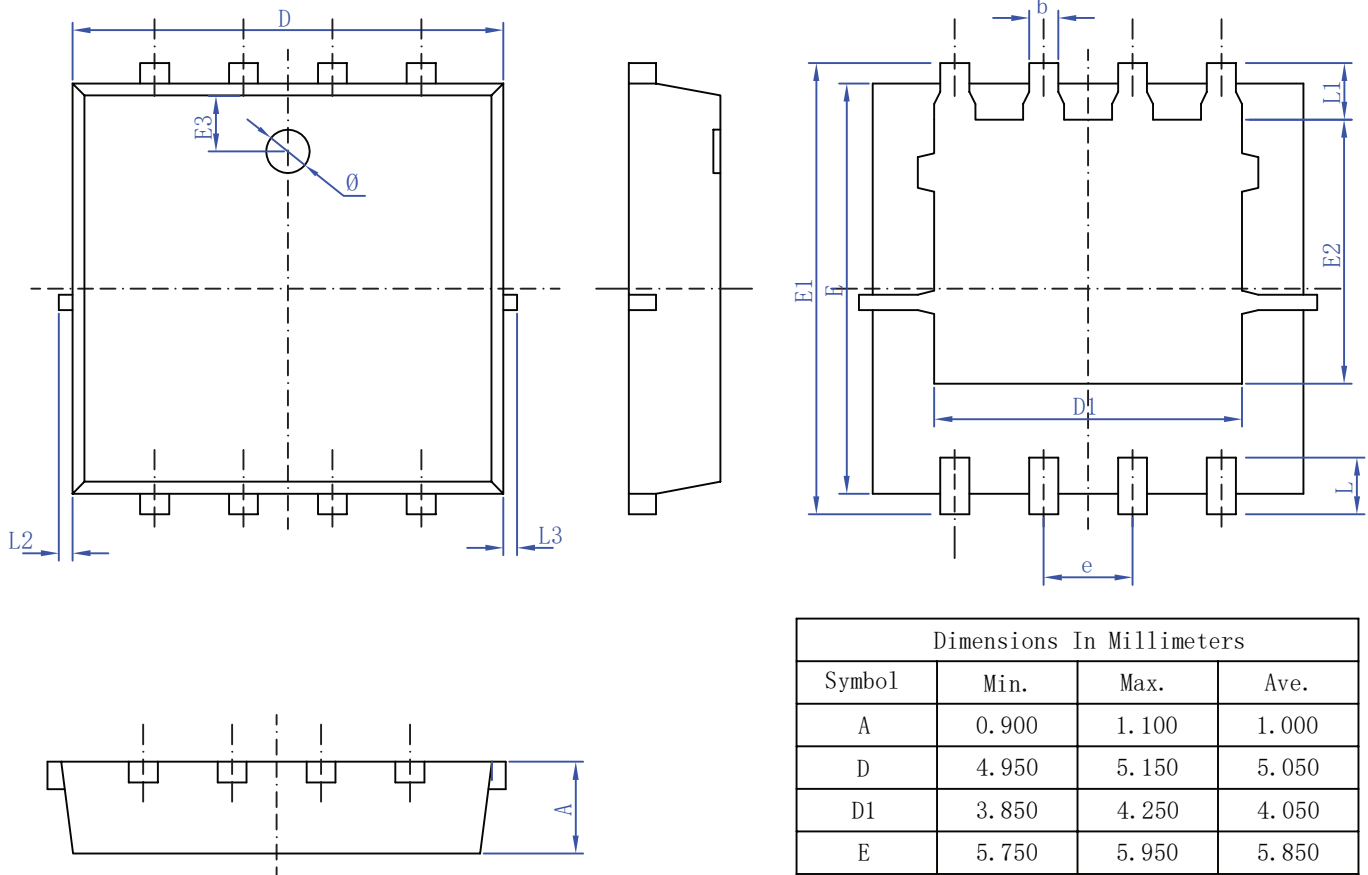
Typical Characteristics



Package Dimension

DFN-8 5x6

Unit :mm



注:

1. 未注公差 ± 0.05 未标注圆角 $R_{\max}=0.25$

Dimensions In Millimeters			
Symbol	Min.	Max.	Ave.
A	0.900	1.100	1.000
D	4.950	5.150	5.050
D1	3.850	4.250	4.050
E	5.750	5.950	5.850
E1	5.950	6.350	6.150
E2	3.300	3.700	3.500
E3	0.900	1.300	1.100
b	0.250	0.350	0.300
e	1.220	1.320	1.270
L	0.585	0.785	0.685
L1	0.525	0.725	0.625
Ø	1.000	1.400	1.200
L2	0~0.100		
L3	0~0.100		